



N-Channel DMOS MOSFET Wafer

Wafer Specification

1200V V_{DS} / $\pm 30V$ V_{GS} N-Channel DMOS MOSFET Wafer	Wafer Name	PTC03N120
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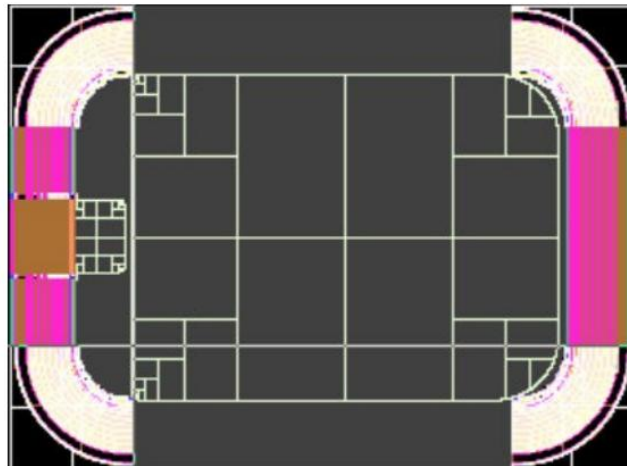
(1) **Key Electrical Characteristics of Die**

Parameter	Description	Min.	Typ.	Max.	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	1200V			$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance		9 Ω		$V_{GS} = 10V, I_D = 1.5A$
$V_{GS(th)}$	Gate Threshold Voltage	2.5V		4.5V	$V_{DS} = V_{GS}, I_D = 250\mu A$
V_{GSS}	Gate-to-Source Voltage			$\pm 30V$	NA
I_{DSS}	Drain-to-Source Leakage Current			1 μA	$V_{DS} = 1200V, V_{GS} = 0V, T_J = 25^\circ C$
I_{GSS}	Gate-to-Source Leakage Current			$\pm 100nA$	$V_{GS} = \pm 30V$
V_{SD}	Body Diode Voltage			1.5V	$V_{GS} = 0V, I_{SD} = 3A$
T_J	Operating Junction and Storage	-55 $^\circ C$ to 150 $^\circ C$ Max			
T_{STG}	Temperature Range				

(2) **Mechanical Data**

Nominal Back Metal Composition, Thickness:	Ag
Nominal Front Metal Composition, Thickness:	Al, 4.0 μm
Dimensions:	3930 μm x 2930 μm (不含划片槽尺寸)
Gate Pad Size:	350 μm x 460 μm
Wafer Diameter:	150mm (6inch)
Source Pad Size	2700 μm x 2040 μm ,without PA layer
Wafer Thickness:	200 $\mu m \pm 15\mu m$
Minimum Street Width:	70 μm
Reject Ink Dot Size:	ink
Recommended Storage Environment:	Store in original container, in desiccated nitrogen, with no contamination
Recommended Die Attach Conditions:	For optimum electrical results

(3) **Die Outline**



Gross die / per 6" wafer =1260 pcs